

Nonequilibrium and Parity Effects in the Tunneling Conductance of Ultrasmall Superconducting Grains

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Recent experiment on the tunneling spectra of ultrasmall superconducting grains revealed an unusual structure of the lowest differential conductance peak for grains in the odd charging states. We explain this behavior by nonequilibrium “gapless” excitations associated with different energy levels occupied by the unpaired electron. These excitations are generated by inelastic cotunneling.

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The electron-electron interaction strongly affects the tunneling transport through ultrasmall metallic grains. Many phenomena of grains in the normal state are described by the orthodox model in which the interaction takes a simple form $E_{\text{int}} = Q^2/(2C)$, where Q and C are the total charge and capacitance of the system respectively¹. This model is successful in describing the Coulomb blockade, which is essentially the quantization of the number of electrons in the grain, when the gate voltage is tuned away from the charge degeneracy point. Because of this quantization, the zero-bias conductance of the system vanishes, while the current I as the function of the source-drain voltage V shows a threshold behavior. Fine structure of the current-voltage curve was attributed to single-electron levels of the system^{2,3}.

However, there is a variety of effects which are not described by the orthodox model. They may become especially pronounced when the system is driven out of equilibrium, thereby exploring many excited states. For normal metallic grains, nonequilibrium steady states were shown to lead to clustering of resonances in the differential conductance due to fluctuations of the interaction energy among electrons⁴. The experimental findings for *normal* metallic grains⁵ can be summarized as follows:

1. Clusters of resonances of the differential conductance spectra appeared at high source-drain voltage for which nonequilibrium configurations of the electrons become energetically allowed. The first peak, however, did not split into several resonances.
2. The width of each resonance cluster was found to be much smaller than the mean level spacing d . It is of order d/g , where $g \sim 5$ is the dimensionless conductance of the grain.

Recently, Ralph *et al.*⁶ measured the tunneling resonance spectra of ultrasmall *superconducting* grains. The number of electrons in the system was controlled by a gate voltage. The results of this experiment show that:

1. For the ground state of the grain with an even number of electrons, the first peak of the differential conductance is merely shifted by the gate voltage V_g . The shape of this peak does not change over

a large interval of V_g . Contrarily, if the grain contains an odd number of electrons, the height of the first peak rapidly reduces with a change of the gate voltage. Moreover, a structure of subresonances develops on the low-voltage shoulder of this peak, see Fig. 1.

2. The characteristic energy scale between subresonances of the first peak is of the order of mean level spacing d .

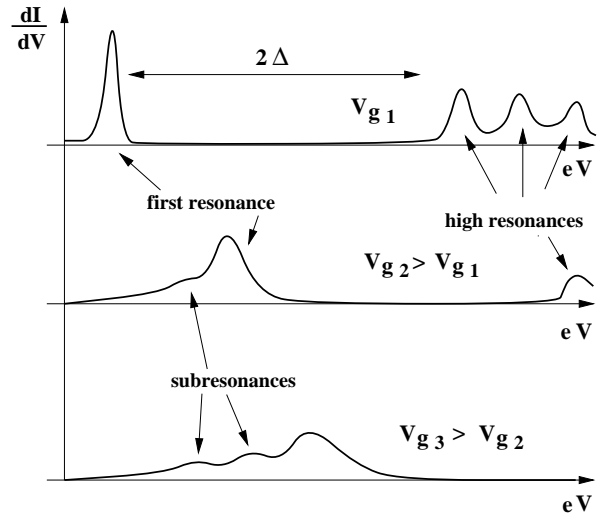


FIG. 1. A schematic illustration of the differential conductance of an “odd” superconducting grain as function of the source-drain voltage V , at various gate voltages V_g . Higher resonances are separated by the superconducting gap from the first one, and subresonances are developed as the first resonance is shifted by the gate voltage.

These observations contrast the results for the normal case, nevertheless, it was suggested⁶ that the substructure of the first peak is still associated with nonequilibrium steady states of the grain. The purpose of this paper is to clarify the origin of these nonequilibrium states and the mechanism which generates them.

The principle difference between odd and even grains is that all excitations of the latter are of energy larger than the superconducting gap 2Δ . Therefore, a source-drain voltage in the range $V < \Delta/e$ can not induce nonequilib-

rium states. Odd grains, on the other hand, contain one unpaired electron, which may be shifted to various single electron levels with characteristic energy scale smaller than the mean level spacing d . For this reason even small source-drain voltage $d < eV < \Delta$ is sufficient to excite the grain. The mechanism of excitation is inelastic cotunneling⁷. Tunneling into the excited grain requires less energetic electrons, and lead in turn to the substructure on the low-voltage shoulder of the of the first resonance, see Fig. 1. A closely related problem was considered by Averin and Nazarov⁸, however, their theory assumed that relaxation processes prevent the formation of nonequilibrium states. For small metallic grains relaxation processes are very slow⁴, and therefore will be neglected in our theory.

To describe the effect quantitatively, we construct the master equations governing the time evolution of probabilities of different electronic configurations of superconducting grains allowing for second order cotunneling processes. The solution of these equations for two limiting cases (one in which two levels participate in the transport, and the other when a large number of levels contribute) explains the substructure of the first peak of the differential conductance illustrated in Fig. 1.

Our model Hamiltonian is given by $\hat{H} = \hat{H}_0 + \hat{H}_T + \hat{H}_{\text{int}}$. Here \hat{H}_0 describes the noninteracting electrons in the left (L) and right (R) leads and in the metallic grain,

$$\hat{H}_0 = \sum_{\nu=L,R} \sum_q (\xi_{\nu q} + \mu_\nu) d_{\nu q}^\dagger d_{\nu q} + \sum_j \xi_j c_j^\dagger c_j. \quad (1)$$

Single particle energies $\xi_{\nu q}$, are measured relative to the chemical potentials of the left $\mu_L = \alpha eV$ and right $\mu_R = (\alpha-1)eV$ leads (the numerical coefficient $0 < \alpha < 1$ depends on the capacitances between the grain and the leads). Tunneling across the barriers is described by

$$\hat{H}_T = \sum_{\nu=L,R} \sum_{q,\alpha} T_{q\nu}^{(\nu)} d_{\nu q}^\dagger c_j + \text{H.c.}, \quad (2)$$

where $T_{qj}^{(\nu)}$ are the tunneling matrix elements. The interaction Hamiltonian is

$$\hat{H}_{\text{int}} = \frac{e^2}{2C} (\hat{N} - N_0)^2 - \lambda \sum_{i,j} c_{i\uparrow}^\dagger c_{i\downarrow}^\dagger c_{j\uparrow} c_{j\downarrow}. \quad (3)$$

The first term in Eq. (3) is the orthodox model for the repulsive part of the electron-electron interaction: C is the total capacitance of the grain, $\hat{N} = \sum_j c_j^\dagger c_j$ is the number of electrons in the dot, and N_0 is a continuous parameter controlled by the gate voltage. N_0 determines the finite charging energy required to insert, U_+ , or to remove, U_- , one electron,

$$U_\pm = \frac{e^2}{C} \left[\frac{1}{2} \pm (N - N_0) \right], \quad |N - N_0| \leq \frac{1}{2}. \quad (4)$$

The second term in Eq. (3) drives the grain to the superconducting state (we assume zero temperature).

We consider the experimentally relevant case, $e^2/C \gg \Delta$, so that the grain has well defined number of electrons. If this number is even $N = 2m$, the ground state energy (we will omit charging part of the energy and restore it later), $E_{2m} = F_{2m} + 2\mu m$, can be calculated in the mean field approximation^{9,10} by minimizing thermodynamic potential $F_{2m} = \sum_k (\xi_k - \epsilon_k) + \Delta^2/\lambda$ where $\epsilon_k = (\xi_j^2 + \Delta^2)^{1/2}$, with respect to Δ ($\partial F/\partial \Delta = 0$), and by fixing the chemical potential via $2m = -\partial F/\partial \mu$. All the excited states of even dots are separated from the ground state by a large energy, 2Δ . Considering now the energy spectrum of an odd grain, $N = 2m - 1$, we notice that the second term in Eq. (3) operates only within spin singlet states. Therefore, to calculate the low-lying excited states in this case, we fill the single-electron state j with one electron, and then find the ground state of the remaining $2m$ electrons with state j excluded from the Hilbert space. In the mean field approximation it corresponds to the minimization of the thermodynamic potential $F_{2m-1}^{(j)} = \sum_{k \neq j} (\xi_k - \epsilon_k) + \Delta^2/\lambda + \xi_j$. The excited states with energies smaller than Δ are characterized by a single index, j and will be denoted by $E_{2m-1}^{(j)}$. In what follows we will need the energy cost of introducing an additional electron into the odd state: $U_+ + \epsilon_j$, where $\epsilon_j = E_{2m} - E_{2m-1}^{(j)}$. Assuming $\Delta \gg d$, one obtains¹¹

$$\epsilon_j = \mu_{2m} - \frac{3d}{2} + \frac{\xi_j d}{2\Delta} - \sqrt{\xi_j^2 + \Delta^2}. \quad (5)$$

We turn now to the kinetics of a superconducting grain. Consider the regime where $U_+ = U \lesssim \Delta$, $U_- \approx \frac{e^2}{2C} \gg U$, and $\frac{e^2}{2C} \gg \Delta \gg d$. We also assume the conductance of the tunnel barriers to be much smaller than e^2/h , and that the source-drain voltage is small $eV < \Delta$. The simplicity brought to the problem in this regime of parameters stems from the fact that there is only one available state with an even number of electrons (because $U_- \gg U_+$ one can only add an electron to grain but not subtract one), and whenever the grain contains an even number of electrons it is in its ground state. This imply that even grains cannot be driven out of equilibrium state, while for odd grains tunneling (and cotunneling) takes place via unique state.

Henceforth, we concentrate on grains with an odd ground state. Let us denote by P_e the probability of finding the grain with an even number of electrons, and by P_j the probability to find the grain in the odd state j . Since these states are spin degenerate in the absence of magnetic field, P_j will denote the sum $P_{j,\uparrow} + P_{j,\downarrow}$. The master equations for the probabilities P_e, P_j have the form

$$\frac{dP_e}{dt} = \sum_j \left[\Gamma_{o \rightarrow e}^{(j)} P_j - 2\Gamma_{e \rightarrow o}^{(j)} P_e \right], \quad (6)$$

$$\frac{dP_j}{dt} = 2 \sum_{i \neq j} [\Gamma_{i \rightarrow j} P_i - \Gamma_{j \rightarrow i} P_j] + 2\Gamma_{e \rightarrow o}^{(j)} P_e - \Gamma_{o \rightarrow e}^{(j)} P_j,$$

where $\Gamma_{o \rightarrow e}^{(j)}$ and $\Gamma_{e \rightarrow o}^{(j)}$ are the transitions rates from the odd j -th state to the even and from the even to odd respectively, while $\Gamma_{i \rightarrow j}$ is the rate of transition from the i -th to the j -th odd states. Equations (6) are not linear independent, so they have to be supplied with the normalization condition $P_e + \sum_j P_j = 1$. Current in the steady state equals to the electron flow through, say, the left barrier, and for positive V it is given by

$$I = e \sum_j \left(\Gamma_{o \rightarrow e}^{(j)} + \Gamma_{j \rightarrow j} \right) P_j + 2e \sum_{j \neq i} \Gamma_{j \rightarrow i}^{(j)} P_j. \quad (7)$$

Transition from the j -th odd state into the even state occurs when $\mu_L > U + \varepsilon_j$. The amplitude of this transition is calculated by first order perturbation theory in the tunneling Hamiltonian (2). Fermi's golden rule yields

$$\Gamma_{o \rightarrow e}^{(j)} = g_L \frac{u_j^2 \rho_{Lj} d}{2\pi\hbar} \theta(\mu_L - \varepsilon_j - U), \quad (8a)$$

where g_L is the dimensionless conductance of the left tunnel barrier per one spin, $u_j = (1 + \xi_j/\varepsilon_j)/2$ is the coherence factor, $\theta(x)$ is the unit step function, and $\rho_{Lj} = \Omega |\psi_j(r_L)|^2$, where Ω is the volume of the grain and $\psi_j(r_L)$ is the value of j -th single particle wave function at the left point contact r_L . Energies ε_i are given by Eq. (5) and $U = U_+$ is defined in Eq. (4). Similarly, the rate of transition from even state to i -th odd state, by tunneling of an electron from the dot to the right lead, is given by

$$\Gamma_{e \rightarrow o}^{(i)} = g_R \frac{v_i^2 \rho_{Ri} d}{2\pi\hbar} \theta(U + \varepsilon_i - \mu_R), \quad (8b)$$

where g_R is the dimensionless conductance of the right tunnel barrier, $v_i = (1 - \xi_i/\varepsilon_i)/2$, and $\rho_{Ri} = \Omega |\psi_i(r_R)|^2$, where r_R is the position of the right point contact.

A change in the occupation configuration of the odd states occurs via inelastic cotunneling⁷. This mechanism is a virtual process in which an electron tunnels into j -th available level and another electron tunnels out from the i -th level. Calculating this rate by second order perturbation theory in the tunneling Hamiltonian, one obtains

$$\Gamma_{j \rightarrow i} = \frac{g_L g_R d^2 u_j^2 v_i^2 \rho_{Lj} \rho_{Ri} (eV - \varepsilon_j + \varepsilon_i)}{8\pi^3 \hbar (U + \varepsilon_j - \mu_L)(U + \varepsilon_i - \mu_R)} \quad (8c)$$

for $eV > \varepsilon_j - \varepsilon_i$, $\mu_L < U + \varepsilon_j$, $\mu_R < U + \varepsilon_i$, and zero otherwise. $\Gamma_{j \rightarrow i}$ diverges in the limits $\mu_L \rightarrow U + \varepsilon_j$ and $\mu_R \rightarrow U + \varepsilon_i$. It signals that a real transition takes over the virtual one. The region of applicability of Eq. (8c) is, therefore, $U + \varepsilon_j - \mu_L > \gamma$ and $U + \varepsilon_i - \mu_R > \gamma$ where $\gamma \sim gd/4\pi$ is the width of a single particle level in the dot due to the coupling to the leads, $g = g_L + g_R$. However, the interval of biases where Eq. (8c) is not valid is narrow, and to the leading approximation in \hat{H}_T our results will be independent of this broadening.

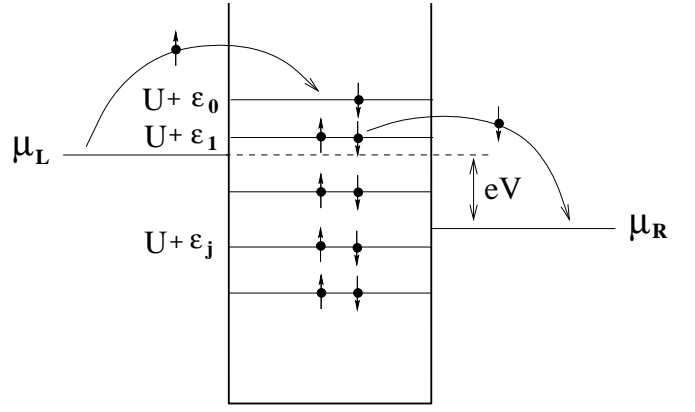


FIG. 2. Inelastic cotunneling process can drive an “odd” superconducting grain out of its ground state. In the ground state, the single particle level indicated by $U + \varepsilon_0$ is occupied by one electron. Excited states are those in which the unpaired electron is shifted to other single particle levels. In a nonequilibrium steady state, low single particle levels become available for resonant tunneling, leading to a subresonance structure of the differential conductance shown in Fig. 1. State j shown to be filled with two electrons should be understood as a coherent superposition of double occupied and empty states with weights v_j^2 and u_j^2 respectively.

Let us now apply Eqs. (6) and (7) to describe the appearance of the low-voltage substructure of the first peak. We will consider two situations: (i) small voltage such that only one subresonance can emerge on the shoulder of the leading one, and (ii) large voltage, $d \ll eV < \Delta$, where the substructure of the main resonance consists of a large number of subresonances.

In the first case, the chemical potentials of the left and right leads are such that transport through the grain involves only two levels: ε_0 and $\varepsilon_1 < \varepsilon_0$ corresponding to the ground and the first excited states of the odd grain. We solve Eqs. (6) for probabilities P_0, P_1 and P_e using Eqs. (7) and (8). There are two distinct regimes of the source-drain voltage: (1) $\mu_L < U + \varepsilon_0$ where transport is dominated by cotunneling, and (2) $\mu_L \geq U + \varepsilon_0$ where state “0” is available for resonant tunneling. The substructure of the first resonance in the differential conductance appears in the first regime. Below we show that as μ_L passes through $U + \varepsilon_1$, see Fig. 2, there is a discontinuity in the current-voltage curve. In the first regime, the total current to the leading approximation in g_L, g_R is a sum of two contributions, $I \simeq I_{eq} + I_{ne}$. The first, $I_{eq} = e\Gamma_{0 \rightarrow 0} + 2e\Gamma_{0 \rightarrow 1}$, is the equilibrium current coming from cotunneling. The second contribution is associated with the nonequilibrium population of state “1” and is given by

$$I_{ne} = 2e\Gamma_{0 \rightarrow 1} \times \begin{cases} \frac{\Gamma_{1 \rightarrow 0} - \Gamma_{0 \rightarrow 1} + 2\Gamma_{1 \rightarrow 1} - 2\Gamma_{0 \rightarrow 0}}{\Gamma_{0 \rightarrow 1} + \Gamma_{1 \rightarrow 0}} & \mu_L < U + \varepsilon_1 \\ 2 \left(1 + \frac{\Gamma_{1 \rightarrow 0}}{\Gamma_{0 \rightarrow 0}} \right) & \mu_L > U + \varepsilon_1 \end{cases}$$

Assuming that the voltage drop $eV = \mu_L - \mu_R$ is larger than the energy difference $d = \varepsilon_0 - \varepsilon_1$, the jump in the nonequilibrium current is:

$$\delta I_{ne} = c_1 e \frac{g_L g_R d^2}{8\pi^2 h d} \left(1 - \frac{\tilde{d}}{eV}\right) \quad eV \sim 2\tilde{d} \quad (9)$$

where $c_1 = 4u_0^2 v_1^2 \rho_{L0} \rho_{R1}$ is a constant of order unity. This jump in the nonequilibrium current leads to the peak in the differential conductance spectra. Formula (9) has simple interpretation. Up to numerical prefactors it is a product of two factors: first is the probability of finding the grain with an unpaired electron in state “1”. It is proportional to $g_R(d/\tilde{d})(1 - \tilde{d}/eV)$, and increases with the voltage V and as $\tilde{d} = \varepsilon_0 - \varepsilon_1 \rightarrow 0$. The second factor is associated with the rate in which the state “1” is filled with an electron, $eg_L d/h$.

The magnitude of the jump (9) should be compared to the jump in the current as μ_L increases above $U + \varepsilon_0$, and real transition via the even state become allowed. To the leading order in g_L and g_R , the current in this regime is

$$I = c_2 e \frac{g_R g_L d}{h(g_L + 4g_R)}, \quad \mu_L > U + \varepsilon_0, \quad (10)$$

where c_2 is a constant of order unity having structure similar to c_1 . Comparing the current jump, δI_{ne} , with that associated with the resonant tunneling, δI , we find

$$\frac{\delta I_{ne}}{\delta I} \simeq \frac{g_L + 4g_R}{8\pi^2}, \quad eV \sim 2\tilde{d}. \quad (11)$$

Thus nonequilibrium population of the excited level of the odd-grain leads to the appearance of a subresonance at small V , however, its height is much smaller than that of the main resonance.

We turn now to the second regime of the parameters, $d \ll eV < \Delta$, in which many levels contribute to the transport. Again, we focus our attention on the cotunneling regime, $\mu_L < U + \varepsilon_0$. We show that the characteristic amplitude of the subresonances in this regime may become comparable to the amplitude of the main peak.

To the leading order in g_L, g_R , and d/Δ , the steady state solution of the rate equations at $\mu_L = U + \varepsilon_1 + 0$ is $P_0 \simeq 1$, while for the other probabilities we have

$$P_e \simeq \frac{\sum_{i \neq 0} \Gamma_{0 \rightarrow i}}{\Gamma_{e \rightarrow 0}^{(0)}}, \quad P_j \simeq 2 \frac{\Gamma_{0 \rightarrow j}}{\Gamma_{o \rightarrow e}^{(j)}} + 2 \frac{\Gamma_{e \rightarrow o}^{(j)}}{\Gamma_{o \rightarrow e}^{(j)}} P_e. \quad (12)$$

The characteristic number of states contributing to the current (7) is large as $\sqrt{\Delta eV}/d$ so that mesoscopic fluctuations of the tunneling rates and of the inter-level spacings may be neglected. Additional large factor, $\sqrt{\Delta eV}/d$, comes from the summation over the levels in Eq. (12), and we find

$$I \simeq \frac{e^2 g_L g_R}{2\pi^2 h} \frac{V \Delta}{\varepsilon_0 - \varepsilon_j}, \quad \begin{cases} d \ll eV \ll \Delta \\ \mu_L = U + \varepsilon_j + 0 \end{cases} \quad (13)$$

Once again, the current jumps each time μ_L passes through $U + \varepsilon_j$. This jump for large j (but still such that $U + \varepsilon_j - \mu_L \ll eV$) scales as $1/j^3$, and the ratio of

the jump at $j = 1$ to the jump at the resonance level (10) is given by

$$\frac{\delta I_{ne}}{\delta I} \simeq \frac{(g_L + 4g_R)}{8\pi^2} \frac{eV \Delta}{\tilde{d} d}, \quad d \ll eV < \Delta. \quad (14)$$

Noticing that $\tilde{d} = \varepsilon_0 - \varepsilon_1 \simeq d^2/2\Delta$, we see that the first subresonance becomes comparable in height to the main one at voltages as small as $eV \simeq 4\pi^2 d^3/\Delta^2 (g_L + 4g_R)$.

We conclude by comparing the above results with the experimental data of Ref. [6]. There $\Delta \approx 5d$, the conductances in the normal state are $g_R \approx 10g_L \approx 1/8$, and the leads are also superconducting. The singularity in the density of states of the leads imply that the effective conductance is increased by factor of 2 – 3. Neglecting inelastic processes and the Josephson coupling, these parameters imply that when $eV \approx 2d$ the ratio of the subresonances amplitude to that of the first resonance is of order one, while at $eV \sim 2\tilde{d} \approx d/5$ it is of order of 1%. It implies that first subresonance peak associated with tunneling into state “1” cannot be resolved, both because its amplitude and its distance from the main peak are too small. However next subresonance appear already at distance of order d from the main resonance, and for $V > 2d$ have an amplitude comparable with the main resonance.

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